

CLAIMS

1. A method for manufacturing a bipolar transistor, characterized by comprising:
 - 5 forming a base layer on a semiconductor substrate;
forming in an insulating film stacked on said base layer a base electrode lead opening and an emitter electrode lead opening at the same time; and
subsequently forming a base electrode lead portion and an emitter
 - 10 electrode lead portion in, respectively, said base electrode lead opening and said emitter electrode lead opening.
2. The method for manufacturing a bipolar transistor as described in claim 1, characterized in that said base electrode lead portion and said
- 15 emitter electrode lead portion are formed from the same conducting film at the same time.
3. A bipolar transistor having a base electrode lead portion consisting of part of a base layer formed on a semiconductor substrate, said bipolar
- 20 transistor characterized in that said base electrode lead portion and an emitter electrode lead portion are formed in correspondence with, respectively, a base electrode lead opening and an emitter electrode lead opening which are formed at the same time in an insulating film on said base layer.
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4. The bipolar transistor as described in claim 3, characterized in that said base electrode lead portion and said emitter electrode lead portion are formed from the same conducting film at the same time.
- 30 5. A method for manufacturing a semiconductor apparatus which has a bipolar transistor having a base electrode lead portion consisting of part

of a base layer formed on a semiconductor substrate, said method characterized by comprising:

forming said base layer;

5 forming in an insulating film stacked on the base layer a base electrode lead opening and an emitter electrode lead opening at the same time; and

subsequently forming the base electrode lead portion and an emitter electrode lead portion in, respectively, the base electrode lead opening and the emitter electrode lead opening, thus forming the bipolar
10 transistor.

6. The method for manufacturing a semiconductor apparatus as described in claim 5, characterized in that said base electrode lead portion and said emitter electrode lead portion are formed from the same
15 conducting film at the same time.

7. A semiconductor apparatus which has a bipolar transistor having a base electrode lead portion consisting of part of a base layer formed on a semiconductor substrate, said semiconductor apparatus characterized in
20 that said bipolar transistor has the base electrode lead portion and an emitter electrode lead portion which are formed in correspondence with, respectively, a base electrode lead opening and an emitter electrode lead opening which are formed at the same time in an insulating film on said base layer.

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8. The semiconductor apparatus as described in claim 7, characterized in that said base electrode lead portion and said emitter electrode lead portion are formed from the same conducting film at the same time.